# Ultra-Broadband Differential Silicon Capacitor Pair UBDC 0402M 2x10nF BV11



**General description** 

UBDC Ultra-Broadband Differential silicon Capacitor pair targets Optical communication system such as ROSA/TOSA, SONET and all optoelectronics as well as High speed data system or products.

The UBDC is suitable for DC blocking and AC coupling applications in all broadband optoelectronics and High-speed data system.

The unique technology of integrated passive device in silicon, developed by Murata Integrated Passive Solutions, offers unique performances with low insertion loss, low reflection and phase stability from 160 kHz to 60 GHz+.

These Ultra-Broadband MOS Silicon Differential Capacitors pairs (UBDC) in silicon have been developed in a semiconductor process, in order to combine ultra-deep trench MOS capacitors for high capacitance value of <u>min 10nF</u> (for kHz–MHz range) and high frequency MIM capacitors for low capacitance value for GHz range), both in a SMT 0402 [1.00 x 0.50 mm].

The UBDC capacitor pair provides very high stability of the capacitance over temperature, voltage variation as well as a very high reliability.

UBDC capacitors have an extended operating temperature ranging from -55 to 150°C, with very low capacitance change over temperature.

Key features

- Ultra-Broadband performance up to 67 GHz
- Resonance free & phase stability
- $100\Omega$  differential characteristic impedance
- Differential insertion loss < 0.9dB up to 60GHz
- Differential return loss > 12dB<sup>(\*)</sup>
- Ultra-high stability of capacitance value:
  - Temperature 70ppm/K (-55 °C to +150 °C)
  - Voltage <-0.1%/Volt</li>
  - Negligible capacitance loss through ageing

- Low profile: 140µm including bump height
- Break down voltage: 11V
- Low leakage current < 100pA
- High reliability
- High operating temperature (up to 150 °C)
- Compatible with high temperature cycling during manufacturing operations (exceeding 300 °C)
- SAC305 40µm bumps after reflow

# Key applications

- ROSA/TOSA
- SONET
- High speed digital logic

- Microwave/millimetre system
- Volume limited applications
- Broadband test equipment

#### (\*) in 100 $\Omega$ differential impedance Microstrip



#### Functional diagram

The next figure provides implementation set-up of the differential capacitor pair (4 connections).

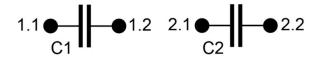


Figure 1: Electrical diagram

#### **Electrical performances**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
С	Capacitance value	@+25°C	10	11.8	13.6	nF
$\Delta C_{P}$	Capacitance tolerance (1)	@+25°C	-15	-	+15	%
T <sub>OP</sub>	Operating temperature		-55	-	150	°C
T <sub>STG</sub>	Storage temperature (2)		-70	-	165	°C
$\Delta C_T$	Capacitance temperature variation	-55 °C to 150 °C	-	70	-	ppm/K
$RV_{DC}$	Rated voltage <sup>(3)</sup>		-	-	3.8 <sup>(4)</sup> 3.4 <sup>(5)</sup>	$V_{\text{DC}}$
BV	Break down voltage	@+25°C	11	-	-	V
$\Delta C_{RVDC}$	Capacitance voltage variation	From 0 V to RV <sub>DC</sub> , @+25°C	-	-	-0.1	%/V <sub>DC</sub>
IR	Insulation resistor	@RV <sub>DC</sub> , +25°C, 120s	-	10	-	GΩ
Fc-3dB	Cut-off frequency at 3dB	@+25°C	-	135	160	kHz
Diff	Diff. characteristic impedance	@+25°C	-	100	-	Ω
		@ 20 GHz, @+25°C	-	0.2	-	dB
	Differential insertion loss $(100\Omega)^{(6)}$ (Microstrip)	@ 40 GHz, @+25°C	-	0.5	-	dB
IL		@ 60 GHz, @+25°C	-	1	-	dB
		@ 20 GHz, @+25°C	-	0.6	-	dB
	Differential return loss (100Ω) (Coplanar)	@ 40 GHz, @+25°C	-	0.8	-	dB
		@ 50 GHz, @+25°C	-	1	-	dB
RL	Differential return loss $(100\Omega)^{(6)}$ (Microstrip)	Up to 60 GHz, @+25°C	-	12	-	dB
	Differential return loss (100Ω) (Coplanar)	Up to 50 GHz, @+25°C	-	12	-	dB
ESD	HBM stress <sup>(7)</sup>	JS-001-2017	2	-	-	kV

Table 1 - Electrical performances

(1): Other tolerance available upon request

(2): Without packaging

(4): Uniform is voltage and temperature dependent, please refer to application note 'Lifetime of 3D capacitors'
(4): 10 years of intrinsic lifetime prediction at 100°C continuous operation

(5): 10 years of intrinsic lifetime prediction at 150°C continuous operation

(6): Simulated based on correlations between simulations and measurement results performed in coplanar mode

(7): please refer to application note 'ESD Challenge in 3D Murata Integrated Passive technology'



#### Simulation results of 2x10nF UBDC in transmission mode on microstrip transmission line

#### **Module S-parameters**

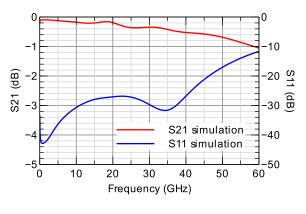


Figure 2 - 2x10nF UBDC simulation results  $(100\Omega \text{ differential})$ 

#### Test bench

#### 4-mils (101µm) Rogers RO4350B

Nominal Pad dimensions – pad length = 0.150 mm, pad width and line width = 0.150 mm, pad gap = 0.100 mm 100 Ohm differential –  $18\mu$ m Cu thickness – full GND plane

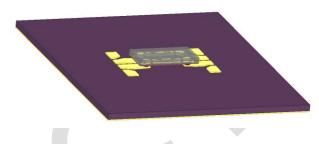


Figure 3 - Microstrip simulation board

# Simulation and Measurements results correlation of 2x10nF UBDC in transmission mode on coplanar transmission line



**Module S-parameters** 

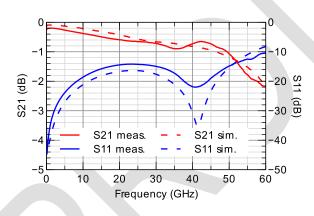


Figure 4 - 2x10nF UBDC measurement results (100Ω differential)

Test bench

#### 25-mils (635µm) alumina 1-3µm Au thickness

Measured with GSSG probes and 4-ports VNA



FREE S-Parameters-Based Linear Simulation Models for ADS

http://www.modelithics.com/mvpmurata.asp

Figure 5 - 2x10nF UBDC soldered on its test board

#### $4x50\Omega$ single ports to $2x100 \Omega$ differential ports transposition (measurement and simulation)

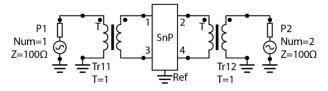
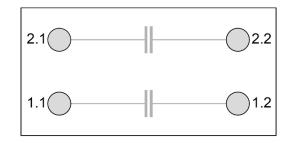


Figure 6 - singe-to-differential transposition



# **Pinning definition**



#### Figure 7 Pinning definition

pin #	Symbol	Coordinates X / Y [µm]
1.1	Signal1	-350.0 / -125.0
1.2	Signal1	350.0 / -125.0
2.1	Signal2	-350.0 / 125.0
2.2	Signal2	350.0 / 125.0

Table 2 - Pining description. Reference (0,0) located at the centre of the die.

### **Ordering Information**

Murata Integrated Passive Devices delivers products with AQL level II (0.65). Tighter quality levels are available upon request.

Part number	Package				
Part number	Packaging	Finishing	Description		
939301421510-F1S	6" film frame carrier <sup>(1)</sup>	SAC <sup>(2)</sup>	UBDC402M – 2x10nF – 4 pads – 1mm x 0.5mm x 0.10 mm <sup>(4)</sup>		
939301421510-T3S	<b>7" T&amp;R</b> with 1Kpieces / reel <sup>(3)</sup>	SAC <sup>(2)</sup>	UBDC402M – 2x10nF – 4 pads – 1mm x 0.5mm x 0.10 mm <sup>(4)</sup>		

Table 3 - Packaging and ordering information

Other film frame carrier are possible on request ENIG + SAC305 type 6 (1)

(2)

missing capacitors can reach 0.5% (3)

(4) Refer to Figure9.

Product Name Die Name		Description			
UBDC421.510	XCA1D510	UBDC 2x10nF/0402M/BV11 – 4 pads – 1 x 0.5 x 0.10 mm			

Table 4 - Die information



#### Pad Metallization

This surface mounted Silicon Capacitor is delivered as standard with SAC305 type 6 bumping (Refer to Figure6). Other Metallization, such as ENIG (0.1µm Au / 5µm Ni) (Refer to Figure7), Copper, Thick Gold or Aluminium pads are possible on request.

UBDC series is compatible with standard reflow process.

It is recommended to design mirror pads on the PCB.

Silicon dies are not sensitive to humidity, please refer to applications notes 'Assembly Notes' section 'Handling precautions and storage'.



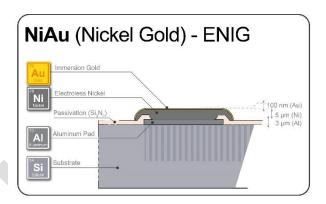


Figure 8 – Top electrode description of SAC305 pre-bumped Figure 9 – Top electrode description of ENIG finishing version version

#### Material regulation

This product is RoHS compliant at the time of publication. For further information about regulation compliancy, please ask your sales representative.

#### Package outline

The product is delivered as a bare silicon die.



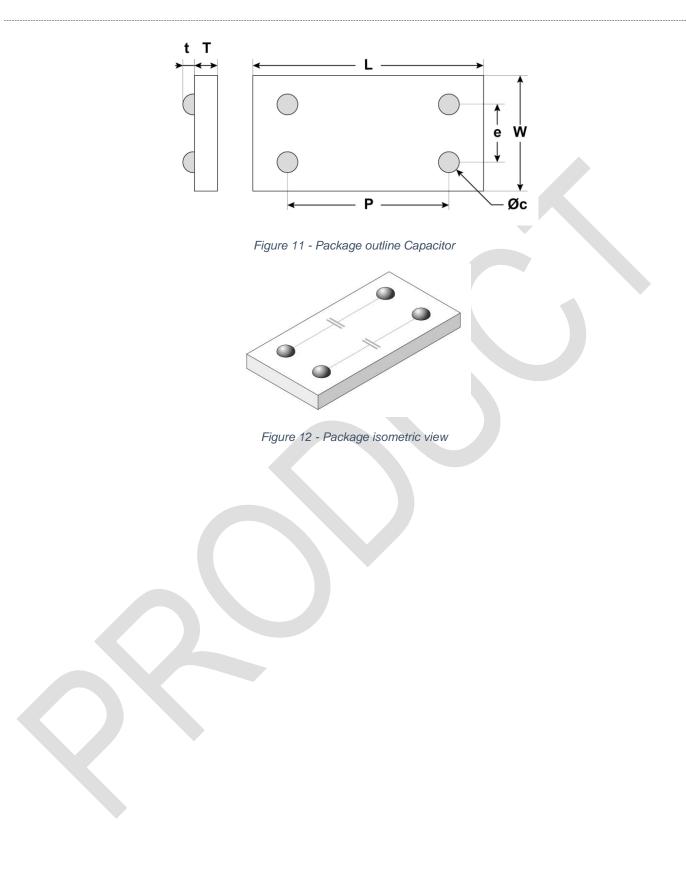
Figure 10 - Micro photography of Capacitor

L (mm)	W (mm)	T (mm)	c (mm)	P (mm)	e (mm)	t (mm)
1.00 ±0.02	$0.50_{\pm 0.02}$	0.10 ±0.015	0.09	0.70	0.25	0.04 <sup>(1)</sup> 0.05 <sup>(2)</sup>

(1) Solder joint height after reflow on board.(2) Solder bump height before assembly

Table 5 - Dimensions and tolerances







#### Assembly

The attachment techniques recommended by Murata on the customer's substrates are fully detailed in specific documents available on our website. To assure the correct use and proper functioning of Murata capacitors please download the assembly instructions on <a href="https://www.murata.com/en-us/products/capacitor/siliconcapacitors">https://www.murata.com/en-us/products/capacitor/siliconcapacitors</a> and read them carefully.



Figure 13 Scan this QR Code to access the Murata Silicon Capacitor web page

#### Packaging format

Please refer to application note 'Products Storage Conditions and Shelf Life'.

#### Tape and Reel:

Dies are flipped in the tape cavity (bump down) with die ID located near the driving holes of the tape.

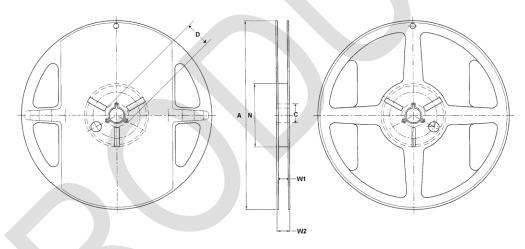


Figure 14 - Reel drawing

Tape Width	Diameter A	С	D	Hub N	W1	W2
8	178 (7 inches)	13.5	20.2	60	9.3	11.5

Table 6 – Reel dimensions (mm)



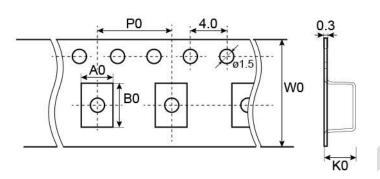


Figure 15 - Tape drawing

Cav	ity dimensi	ions	Carrier tape	Carrier tape	Reel	
Ao	Во	Ко	width W0	pitch P0	Capacity	
0.59	1.09	0.20	8	4	1000	

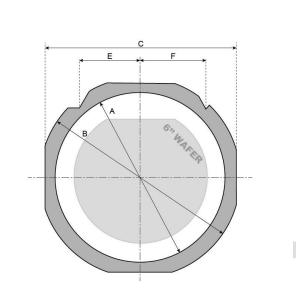
Table 7 - Tape dimensions (mm)



#### Film frame carrier:

With UV curable dicing tape (UV performed).

Good dies are identified using the SINF electronic mapping format. No ink is added on wafer to label other dies.



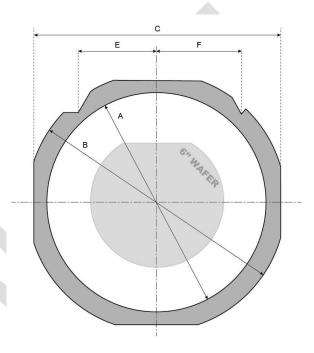


Figure 16 FF070 Frame with a 6" wafer

Figure 17 FF108 Frame with a 6" wafer

Frame Reference	Frame Style	Inside diameter A	Outside diameter B	Width C	Thickness	Pin location E	Pin location F
FF070 <sup>(1)</sup>	DTF-2-6-1	7.638"	8.976"	8.346"	0.048"	2.370"	2.5"
FF108 <sup>(1)</sup>	DTF-2-8-1	9.842"	11.653"	10.866"	0.048"	2.381"	2.5"

Table 8 - Frame dimensions (inches)

(1) or equivalent



### Definitions

#### Data sheet status

**Objective specification:** This data sheet contains target or goal specifications for product development.

**Preliminary specification:** This data sheet contains preliminary data; supplementary data may be published later.

Product specification: This data sheet contains final product specifications.

#### Limiting values

Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those given in the Electrical performances sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### Application information

Where application information is given, it is advisory and does not form part of the specification.

Revision	Date	Description	Author
Release 1.00	2017 Sept. 15th	Objective specification	OGA + SBO
Release 1.09	2020 April 20th	General update	OGA
Release 1.10	2021 Jan 15th	Drawings and template update	OGA+DDE+LLE+ SCA+CGU
Release 2.00	2021 April 23rd	New template and drawings. Preliminary status Update graphs	SCA+OGA+LLR
Release 2.01	2021 June 25th	Minor update	SCA+OGA+LLR
Release 3.01	2023 May 25th	Finishing cross section added	SCA+OGA+LLR

#### **Revision history**

#### Disclaimer / Life support applications

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Murata customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Murata for any damages resulting from such improper use or sale.

Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent or other industrial or intellectual property rights.

Murata Integrated Passive Solutions S.A. makes no representation that the use of its products in the circuits described herein, or the use of other technical information contained herein, will not infringe upon existing or future patent rights. The descriptions contained herein do not imply the granting of licenses to make, use, or sell equipment constructed in accordance therewith. Specifications are subject to change without notice.



www.murata.com

mis@murata.com

